Elektronische Bauelemente

2SD596

0.7A , 30V

NPN Plastic Encapsulated Transistor

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

- High DC Current gain
- Complementary to 2SB624

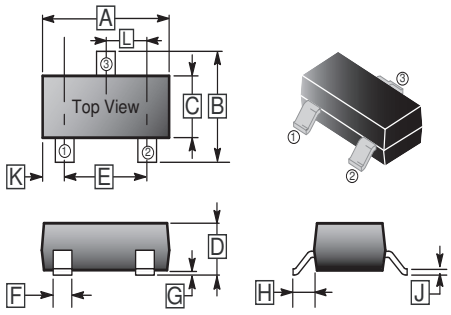
MARKING

DV4

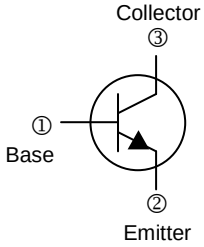
PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch

SOT-23



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.80	3.04	G	0.09	0.18
B	2.10	2.55	H	0.45	0.60
C	1.20	1.40	J	0.08	0.177
D	0.89	1.15	K	0.6 REF.	
E	1.78	2.04	L	0.89	1.02
F	0.30	0.50			



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	700	mA
Collector Power Dissipation	P_C	200	mW
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

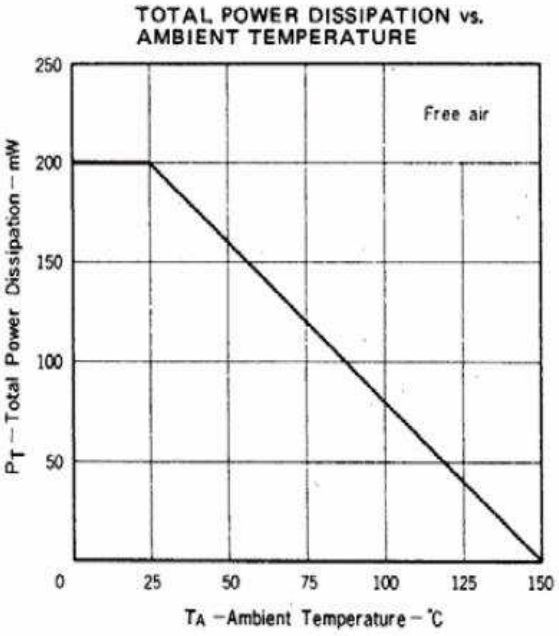
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

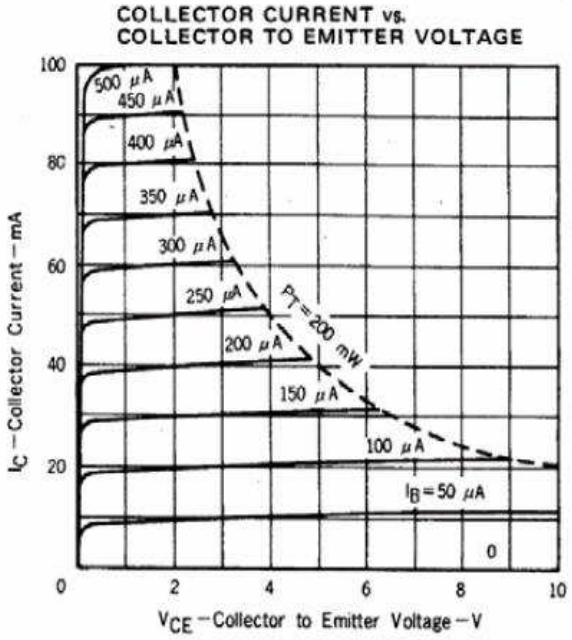
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	30	-	-	V	I_C=100μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	25	-	-	V	I_C=1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=100μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	0.1	μA	V_{CB}=30V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	0.1	μA	V_{EB}=5V, I_C=0
DC Current Gain [1]	$h_{FE\ (1)}$	200	-	320		V_{CE}=1V, I_C=100mA
	$h_{FE\ (2)}$	50	-	-		V_{CE}=1V, I_C=700mA
Collector to Emitter Saturation Voltage [1]	$V_{CE(sat)}$	-	-	0.6	V	I_C=700mA, I_B=70mA
Base to Emitter Saturation Voltage [1]	V_{BE}	0.6	-	0.7	V	V_{CE}=6V, I_C=10mA
Transition Frequency	f_T	170	-	-	MHz	V_{CE}=6V, I_C=10mA
Collector output capacitance	C_{ob}	-	12	-	pF	V_{CB}=6V, I_E=0, f=10MHz

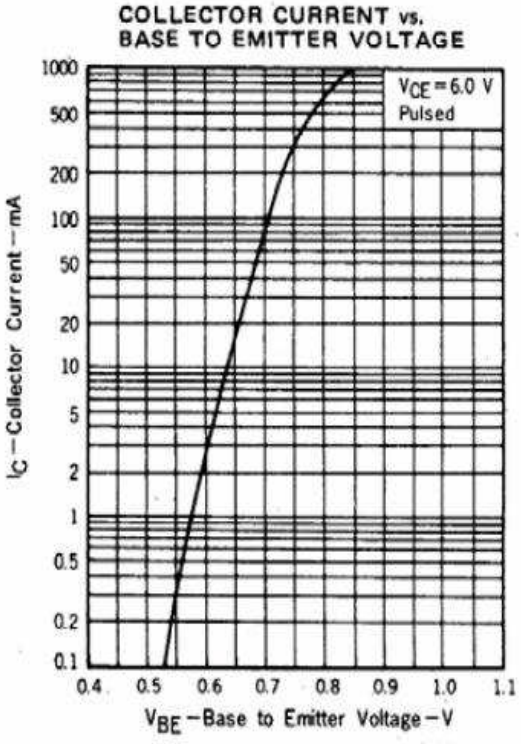
Note:

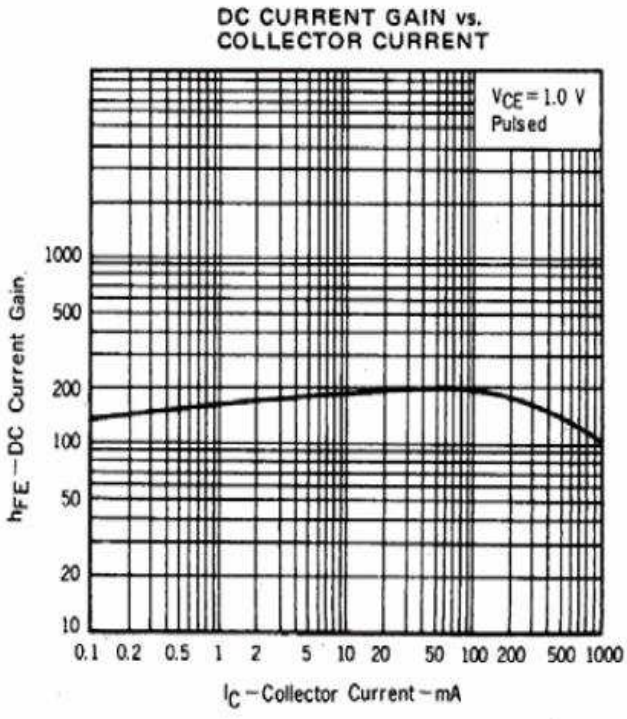
1. Pulse width≦350μs, Duty Cycle≦2%.

CHARACTERISTIC CURVES









CHARACTERISTIC CURVES